

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	15.1449	1.9512	N/A
RT2	5.8098	3.3199	N/A
RT3	6.7345	2.9021	N/A
RT4	32.3108	3.3268	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.0850	132.5103 μ	N/A
CT2	314.1283 μ	624.5588 μ	N/A
CT3	53.8890 m	2.2256 m	N/A
CT4	3.4557	22.9367 m	N/A

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.



R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	6.1902	3.4844	N/A
RF2	7.8428	2.3678	N/A
RF3	22.7933	2.1738	N/A
RF4	23.1737	3.4740	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	342.0201 u	117.7446 u	N/A
CF2	63.0948 m	546.5290 u	N/A
CF3	801.7348 m	102.2644 u	N/A
CF4	3.6448	18.0658 m	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

